





	Some facts
Worldwide oil co	nsumption 2008
USA	19.4 Million barrels/day
China	8.3
Japan	4.8
India	2.9
Russia	2.8
Germany	2.5
Brazil	2.4
South Korea	2.3
Canada	2.3
Saudi Arabia	2.2
France	1.9
Worldwide	84
Minus 0.6%	6 over 2007



























- LED backlighting for laptops (52% in 2009 to 100% in 2012)
- LED TV growing fast
- MEMS-based devices to replace LCD, plasma, OLED? TMOS (Time-Multiplexed Optical Shutter), DMS (Digital Micro Shutter), iMoD (interferometric MoDulator)? For small sizes only probably































- Electric cars will help on oil consumption on the roads, but they need an electrical source... (if all cars in France: +25% to +50% electrical consumption....) total process may be not very efficient \$ value of batteries: ~ 30%, \$ value of electronics... 70% power stations to recharge... ???
- Various types of hybrid cars can save oil consumption with stop-start, use of electrical power for acceleration, regenerative braking, electrical transmission,... Many DC-DC converters needed, DC-AC needed, etc.
- Conventional cars: replacement of wiring by electrical networks save weight, hence consumption, replacement of the lighting by LEDs,....


























































































The worst....?

China projects: coal liquefaction to serve as diesel.... (cf. WW2) = very huge CO_2 emission + huge H₂O quantity required.

Depends on crude oil cost....

And... SO₂ in addition to CO₂: SO₂ blocks solar rays...

The best....?

China projects: gigantic PV power generation to power batteries...

The worst or the best....?

Incentives in various countries to buy EVs: cash rebates, tax credits, import duties withdrawn, use of carpool lanes with no passenger,....


























































































































































e.g. full adder, based on .18µ (- MTJs on top of M4 - manufactured - CMOS vs. MCMOS	CMOS	
	CMOS	мсмоз
Dynamic power (@ 500 MHz)	71.1 µW	16.3 μW
Static power	0.9nW	0.0nW
Area	333 µm²	315 µm²
Device count	42 MOSs	34 MOSs + 4 MTJs
 → Dynamic Current-Mode Log → V_{th} variation compensation (→ RF circuits, LED,) 	jic	
		Ć































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